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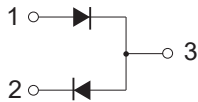
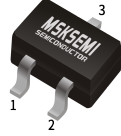
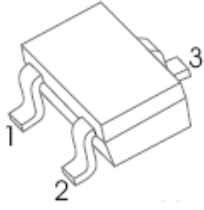
GDT



PLED

Product data sheet

[www.msksemi.com](http://www.msksemi.com)



**SOT-323**

## BAV99W SWITCHING DIODE

### FEATURES

- For high-speed switching applications
- Connected in series

**MARKING: KJG**

### Maximum Ratings @Ta=25°C

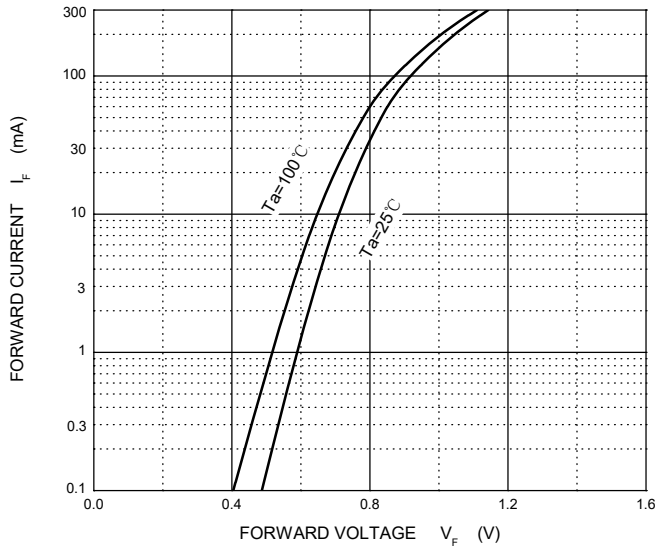
Parameter	Symbol	Limit	Unit
Reverse Voltage	$V_R$	75	V
Forward Current	$I_F$	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	$I_{FSM}$	2.0	A
Power Dissipation	$P_D$	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature range	$T_{STG}$	-55~+150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

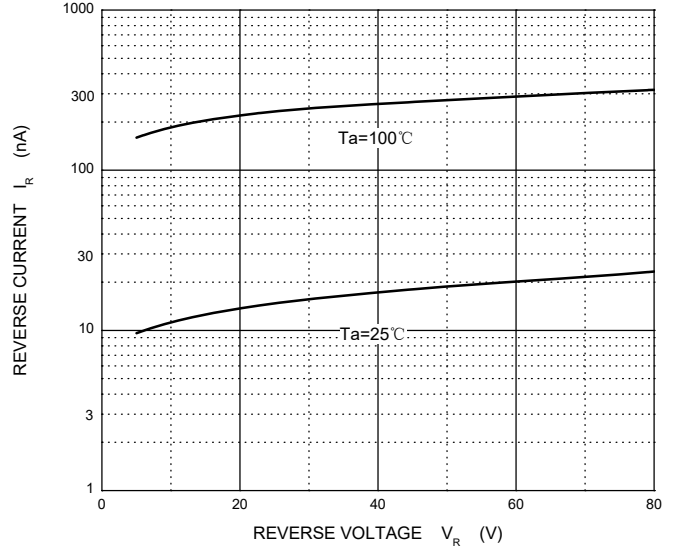
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	$I_{R1}$	$V_R=75V$		2.5	$\mu A$
	$I_{R2}$	$V_R=25V$		25	nA
Forward voltage	$V_F$	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	$C_D$	$V_R=0$ $f=1MHz$		2	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$		4	ns

**Typical Characteristics**

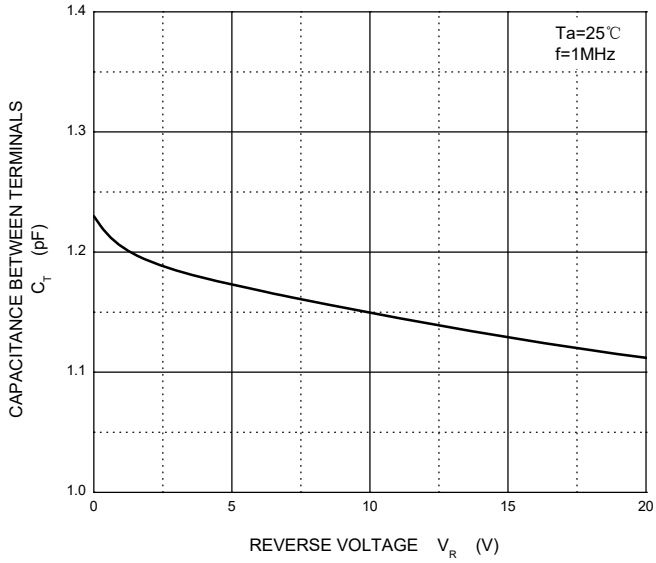
**Forward Characteristics**



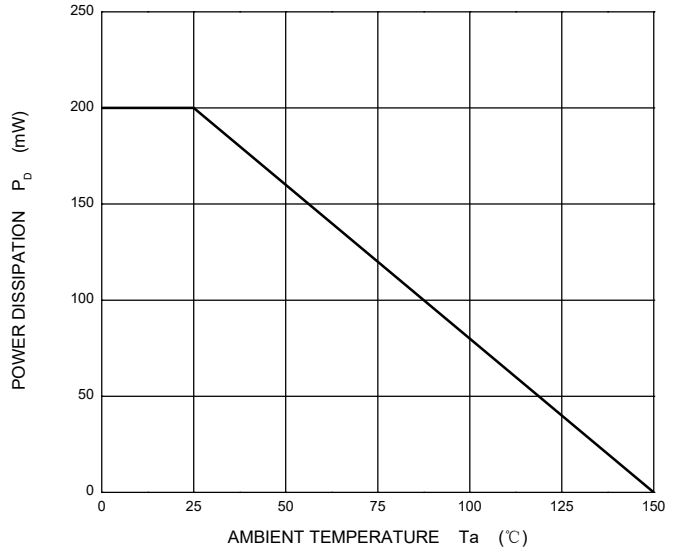
**Reverse Characteristics**



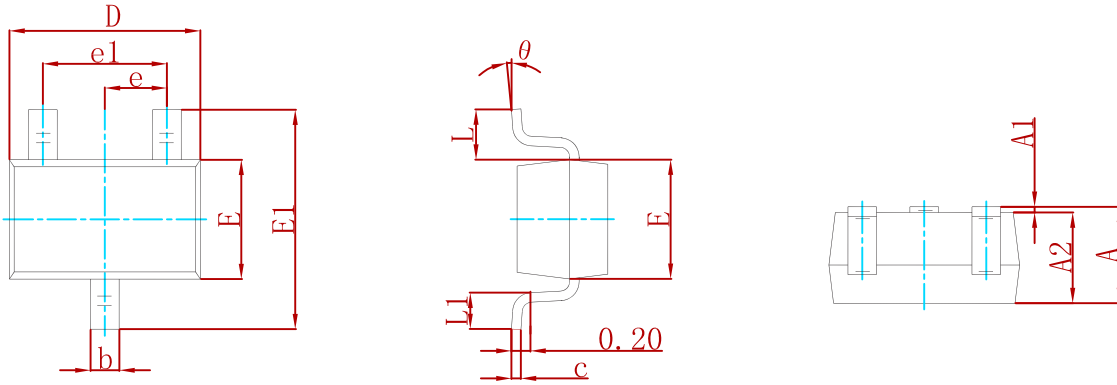
**Capacitance Characteristics**



**Power Derating Curve**

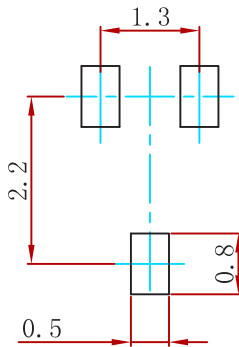


**PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

**Suggested Pad Layout**



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance: ±0.05mm.  
 3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
BAV99W	SOT-323	3000

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